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A1
cont


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- [(amended)] The CMP process as claimed in claim 1,
wherein
the auxiliary layer has a layer thickness in the range of 20 to 100 nm.
3. [(amended)] The CMP process as claimed in claim 1,
wherein
the auxiliary layer is used at least partly as a hard mask for the patterning and preceding
the etching by dry etching.
4. [(amended)] The CMP process as claimed in claim 1,
wherein
the reaching of the auxiliary layer is detected by an etching stop detection signal during
the CMP process.
5. [(amended)] The CMP process as claimed in claim 1,
wherein
an additional wet-chemical cleaning step is carried out at the end of the etching.
6. [(amended)] The CMP process as claimed in claim 1,
wherein
the auxiliary layer is composed of diamond-like carbon, carbon polymers or of porous

7. ~~[(amended)]~~ The CMP process as claimed in claim 6,
wherein

Respectfully submitted,

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